

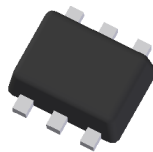
40V COMPLEMENTARY NPN/PNP SMALL SIGNAL TRANSISTOR IN SOT963
Features

- $BV_{CEO} > 40V$
- $I_C = 200mA$ Collector Current
- SOT963 Ultra Small Package of $1mm^2$ Footprint
- Epitaxial Planar Die Construction
- Ideally Suited for Automated Assembly Processes
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

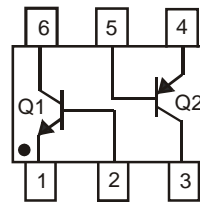
Mechanical Data

- Case: SOT963
- Case Material: Molded Plastic "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208(3)
- Weight: 0.0027 grams (Approximate)

SOT963



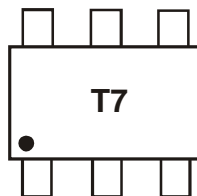
Top View


 Top View
Device Schematic
and Pin-Out

Ordering Information (Note 4)

Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DST3946DPJ-7	T7	7	8	10,000
DST3946DPJ-7B	T7	7	8	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information


T7 = Product Type Marking Code

Absolute Maximum Ratings - NPN (Q1) (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	I _C	200	mA

Absolute Maximum Ratings - PNP (Q2) (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current	I _C	-200	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	300	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	417	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Note: 5. Device mounted on FR-4 PCB with minimum recommended pad layout.

ESD Rating (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	B

Note: 6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

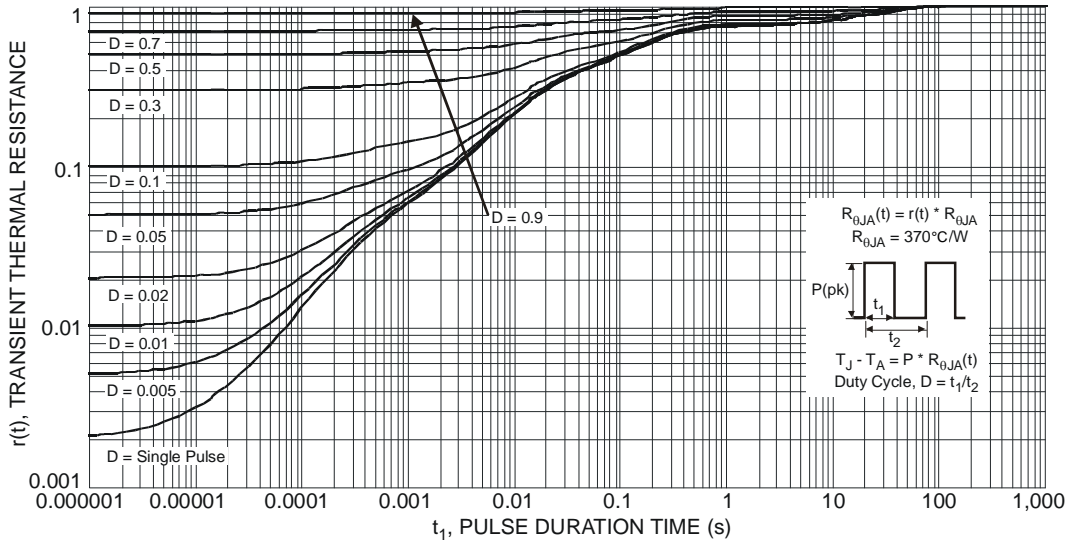


Fig. 1 Transient Thermal Response

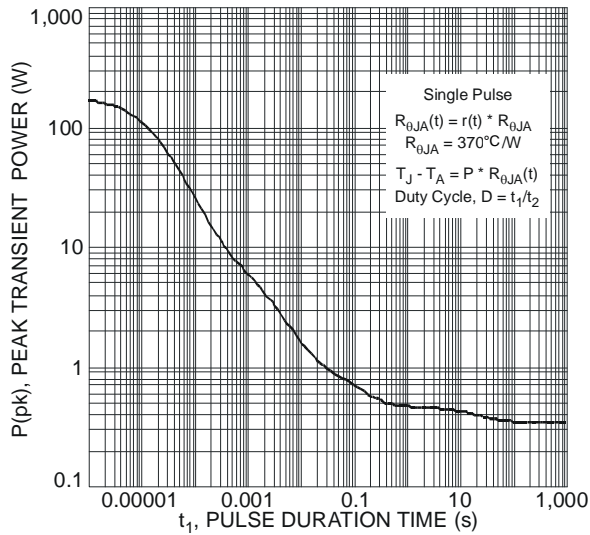


Fig. 2 Single Pulse Maximum Power Dissipation

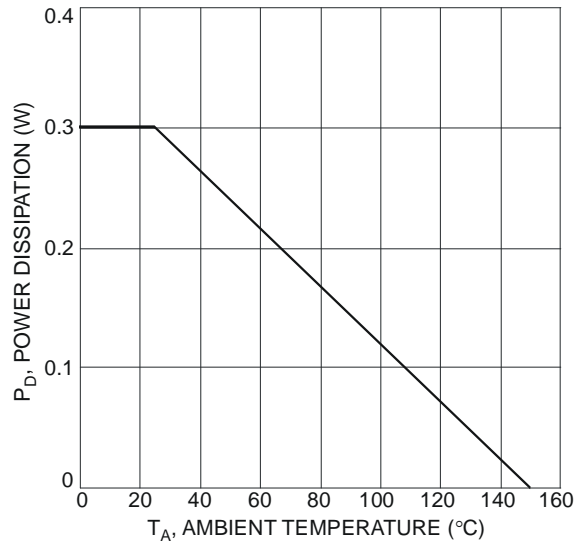


Fig. 3 Power Dissipation vs. Ambient Temperature

Electrical Characteristics - NPN (Q1) (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)					
Collector-Base Breakdown Voltage	BV _{CBO}	60	—	V	I _C = 10μA, I _E = 0
Collector-Emitter Breakdown Voltage (Note 7)	BV _{CEO}	40	—	V	I _C = 1.0mA, I _B = 0
Emitter-Base Breakdown Voltage	BV _{EBO}	6.0	—	V	I _E = 10μA, I _C = 0
Collector Cutoff Current	I _{CEX}	—	50	nA	V _{CE} = 30V, V _{EB(OFF)} = 3.0V
Base Cutoff Current	I _{BL}	—	50	nA	V _{CE} = 30V, V _{EB(OFF)} = 3.0V
ON CHARACTERISTICS (Note 7)					
DC Current Gain	h _{FE}	40	—	—	I _C = 100μA, V _{CE} = 1.0V
		70	—		I _C = 1.0mA, V _{CE} = 1.0V
		100	300		I _C = 10mA, V _{CE} = 1.0V
		60	—		I _C = 50mA, V _{CE} = 1.0V
		30	—		I _C = 100mA, V _{CE} = 1.0V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	0.20 0.30	V	I _C = 10mA, I _B = 1.0mA I _C = 50mA, I _B = 5.0mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	0.65 —	0.85 0.95	V	I _C = 10mA, I _B = 1.0mA I _C = 50mA, I _B = 5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{OBO}	—	4.0	pF	V _{CB} = 5.0V, f = 1.0MHz, I _E = 0
Input Capacitance	C _{IBO}	—	8.5	pF	V _{EB} = 0.5V, f = 1.0MHz, I _C = 0
Input Impedance	h _{iE}	1.0	10	kΩ	V _{CE} = 10V, I _C = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h _{RE}	0.5	8.0	x 10 ⁻⁴	
Small Signal Current Gain	h _{FE}	100	400	—	
Output Admittance	h _{oE}	1.0	40	μs	
Current Gain-Bandwidth Product	f _T	300	—	MHz	V _{CE} = 20V, I _C = 10mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d	—	35	ns	V _{CC} = 3.0V, I _C = 10mA, V _{BE(OFF)} = -0.5V, I _{B1} = 1.0mA
Rise Time	t _r	—	35	ns	
Storage Time	t _s	—	200	ns	V _{CC} = 3.0V, I _C = 10mA, I _{B1} = -I _{B2} = 1.0mA
Fall Time	t _f	—	50	ns	

Note: 7. Short duration pulse test used to minimize self-heating effect.

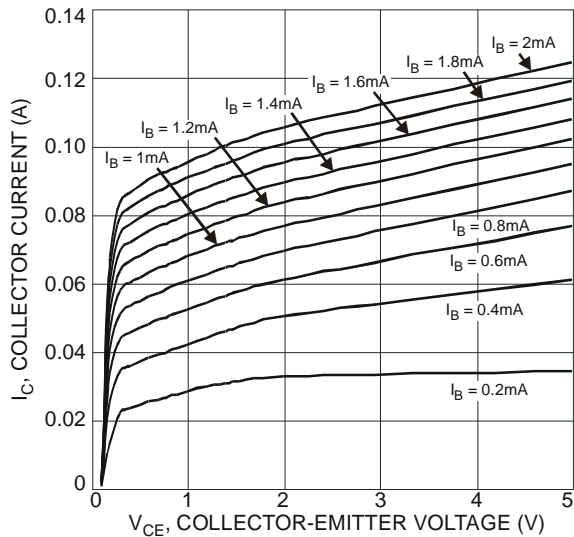


Fig. 4 Typical Collector Current vs. Collector-Emitter Voltage

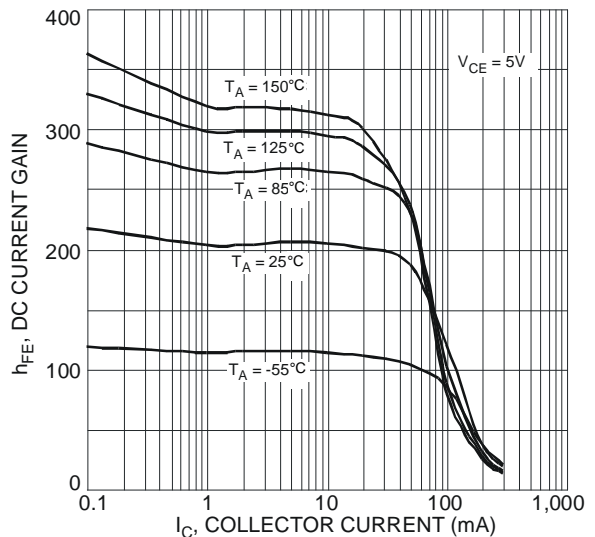


Fig. 5 Typical DC Current Gain vs. Collector Current

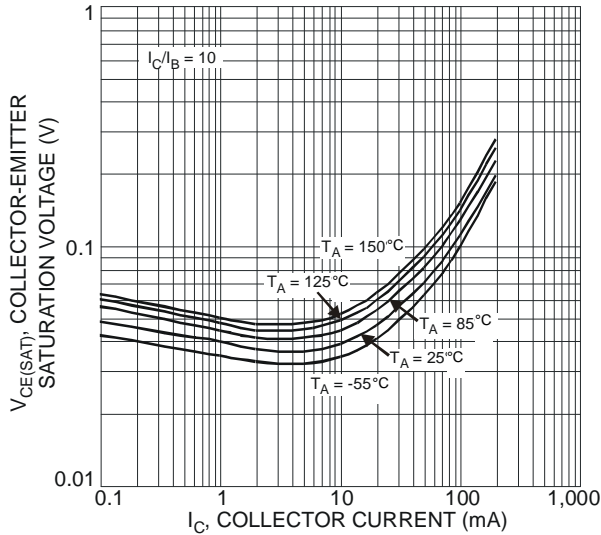


Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current

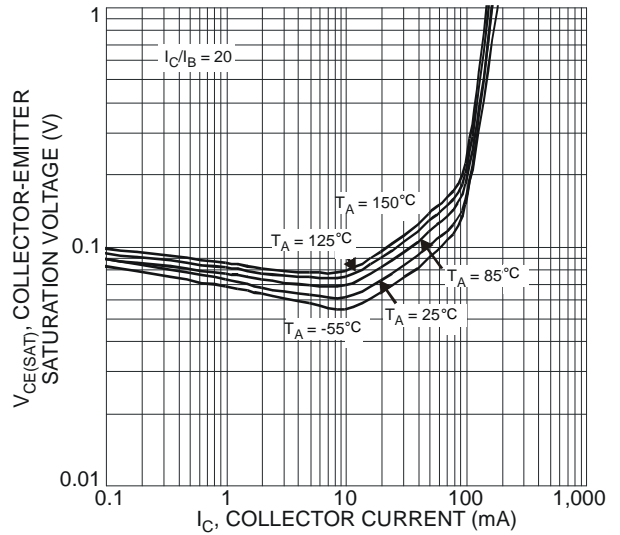


Fig. 7 Typical Collector-Emitter Saturation Voltage vs. Collector Current

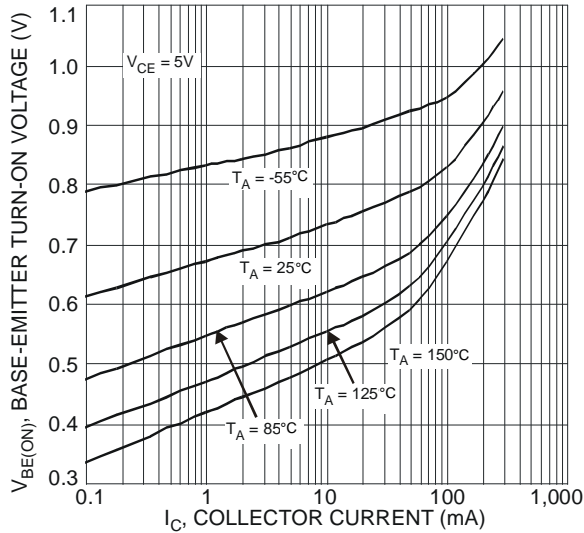


Fig. 8 Typical Base-Emitter Turn-On Voltage vs. Collector Current

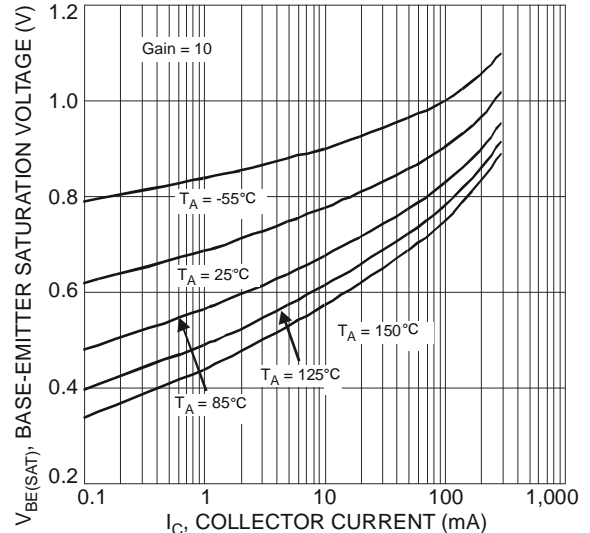


Fig. 9 Typical Base-Emitter Saturation Voltage vs. Collector Current

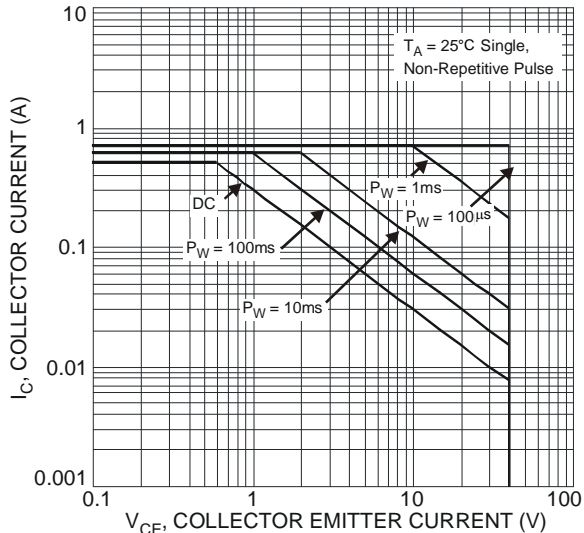


Fig. 10 Safe Operation Area (NPN)

Electrical Characteristics - PNP (Q2) (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV_{CBO}	-40	—	V	$I_C = -10\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 8)	BV_{CEO}	-40	—	V	$I_C = -1.0\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	-5.0	—	V	$I_E = -10\mu\text{A}, I_C = 0$
Collector Cutoff Current	I_{CEX}	—	-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -3.0\text{V}$
	I_{CBO}	—	-50	nA	$V_{CE} = -30\text{V}, I_E = 0$
Base Cutoff Current	I_{BL}	—	-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -3.0\text{V}$
ON CHARACTERISTICS (Note 8)					
DC Current Gain	h_{FE}	60	—	—	$I_C = -100\mu\text{A}, V_{CE} = -1.0\text{V}$
		80	—		$I_C = -1.0\text{mA}, V_{CE} = -1.0\text{V}$
		100	300		$I_C = -10\text{mA}, V_{CE} = -1.0\text{V}$
		60	—		$I_C = -50\text{mA}, V_{CE} = -1.0\text{V}$
		30	—		$I_C = -100\text{mA}, V_{CE} = -1.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	-0.25 -0.40	V	$I_C = -10\text{mA}, I_B = -1.0\text{mA}$ $I_C = -50\text{mA}, I_B = -5.0\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	-0.65 —	-0.85 -0.95	V	$I_C = -10\text{mA}, I_B = -1.0\text{mA}$ $I_C = -50\text{mA}, I_B = -5.0\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{OBO}	—	4.5	pF	$V_{CB} = -5.0\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	C_{IBO}	—	10	pF	$V_{EB} = -0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$
Input Impedance	h_{iE}	2.0	12	k Ω	$V_{CE} = -10\text{V}, I_C = -1.0\text{mA}, f = 1.0\text{kHz}$
Voltage Feedback Ratio	h_{rE}	0.1	10	$\times 10^{-4}$	
Small Signal Current Gain	h_{fE}	100	400	—	
Output Admittance	h_{oE}	3.0	60	μs	
Current Gain-Bandwidth Product	f_T	300	—	MHz	
SWITCHING CHARACTERISTICS					
Delay Time	t_D	—	35	ns	$V_{CC} = -3.0\text{V}, I_C = -10\text{mA}, V_{BE(OFF)} = 0.5\text{V}, I_{B1} = -1.0\text{mA}$
Rise Time	t_R	—	35	ns	
Storage Time	t_S	—	225	ns	$V_{CC} = -3.0\text{V}, I_C = -10\text{mA}, I_{B1} = -I_{B2} = -1.0\text{mA}$
Fall Time	t_F	—	75	ns	

Note: 8. Short duration pulse test used to minimize self-heating effect.

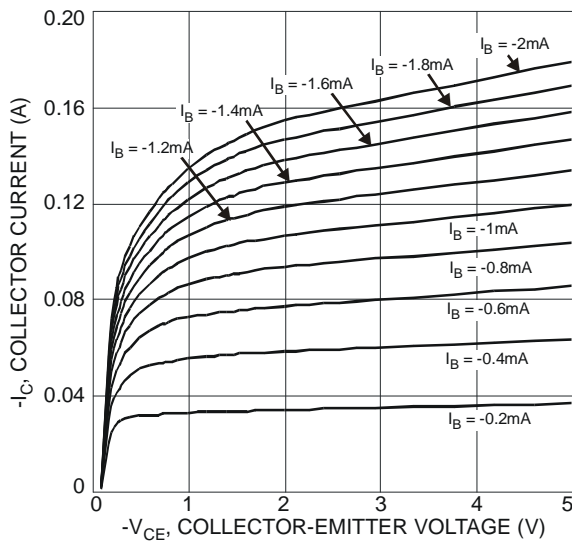


Fig. 11 Typical Collector Current vs. Collector-Emitter Voltage

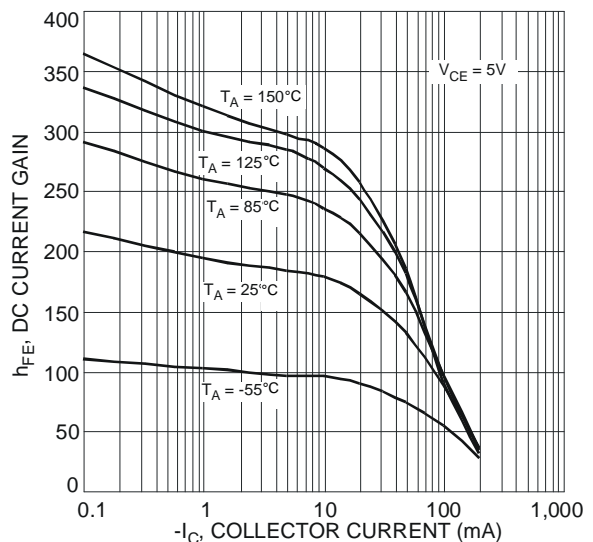


Fig. 12 Typical DC Current Gain vs. Collector Current

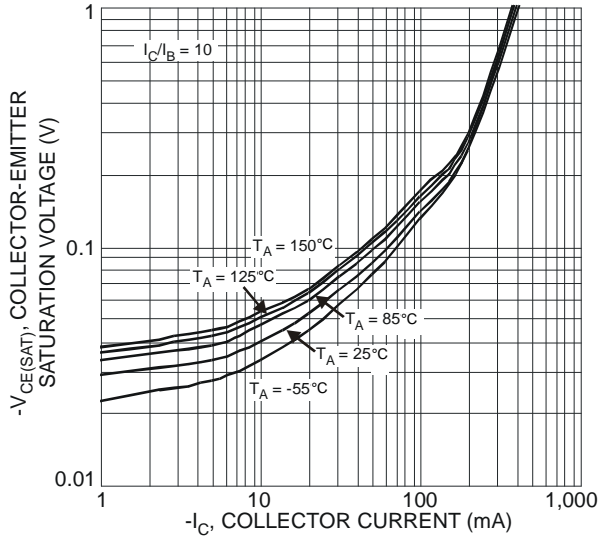


Fig. 13 Typical Collector-Emitter Saturation Voltage vs. Collector Current

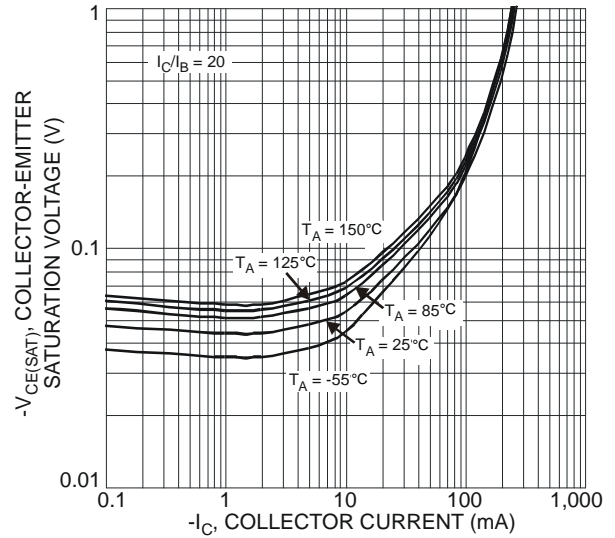


Fig. 14 Typical Collector-Emitter Saturation Voltage vs. Collector Current

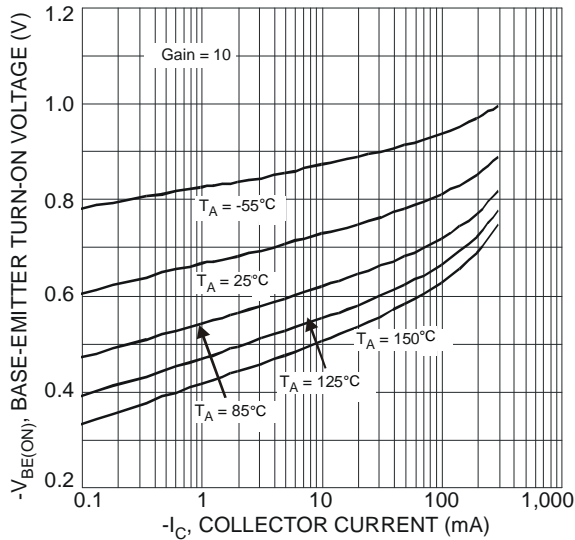


Fig. 15 Typical Base-Emitter Saturation Voltage vs. Collector Current

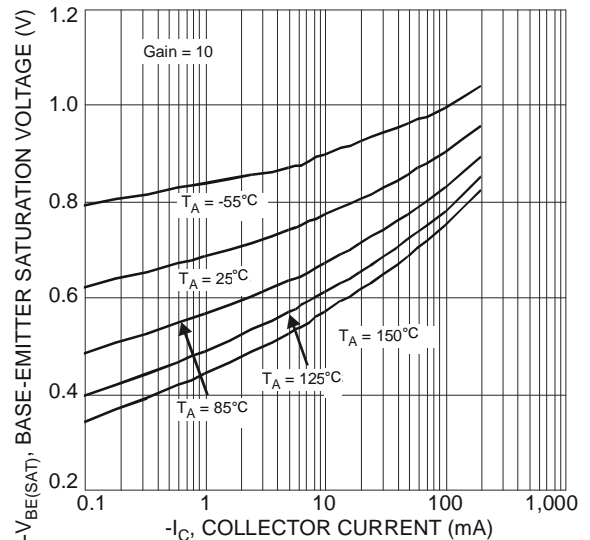


Fig. 16 Typical Base-Emitter Saturation Voltage vs. Collector Current

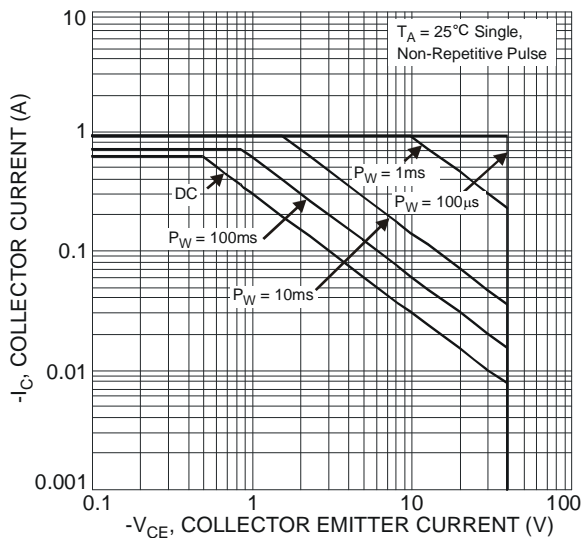
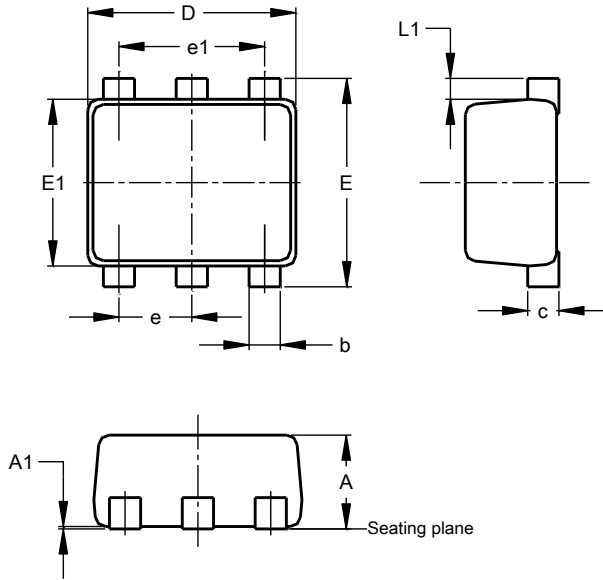


Fig. 17 Safe Operation Area (PNP)

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT963

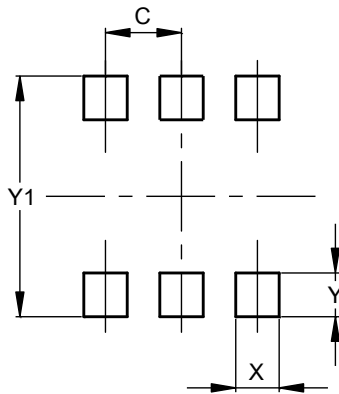


SOT963			
Dim	Min	Max	Typ
A	0.40	0.50	0.45
A1	0.00	0.05	--
b	0.10	0.20	0.15
c	0.120	0.180	0.150
D	0.95	1.05	1.00
E	0.95	1.05	1.00
E1	0.75	0.85	0.80
e	--	--	0.35
e1	--	--	0.70
L1	0.05	0.15	0.10
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT963



Dimensions	Value (in mm)
C	0.350
X	0.200
Y	0.200
Y1	1.100

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